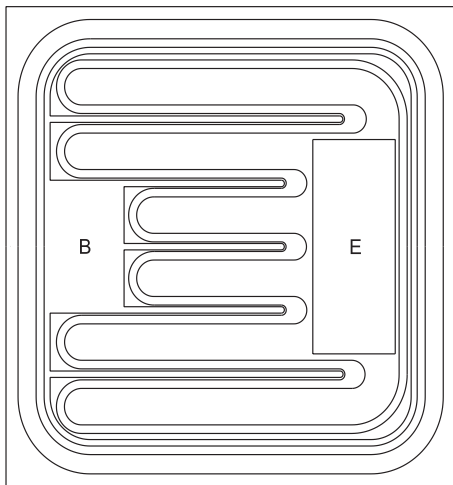


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	87 x 87 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	24 x 15 MILS
Emitter Bonding Pad Area	38 x 16 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Ti/Ni/Ag - 11,000Å

**GEOMETRY**



BACKSIDE COLLECTOR R0

**GROSS DIE PER 4 INCH WAFER**

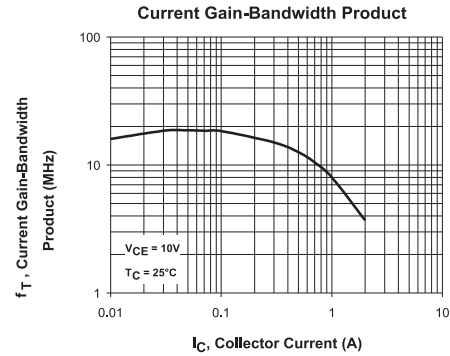
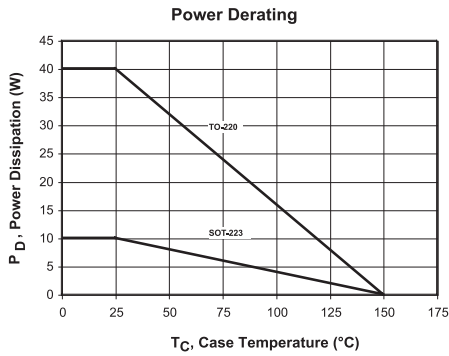
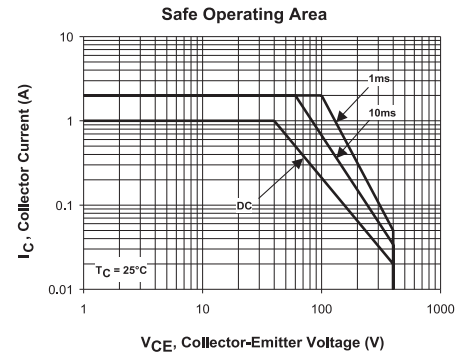
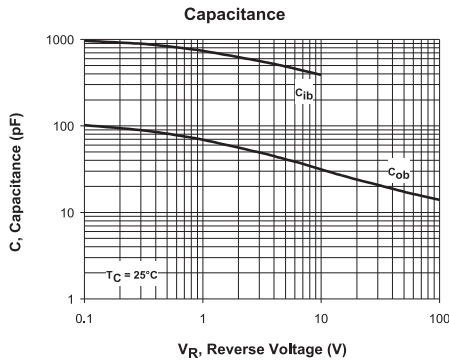
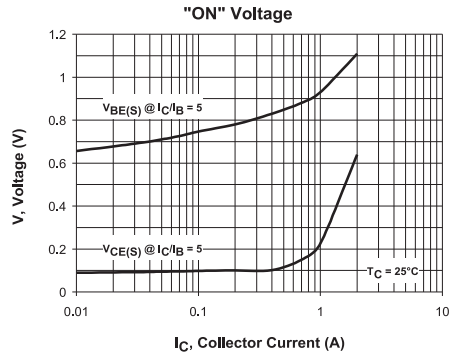
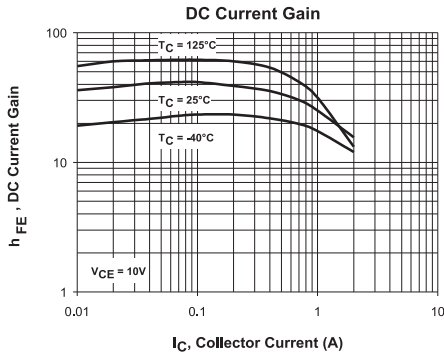
1,460

**PRINCIPAL DEVICE TYPES**

CZTA44HC  
TIP47  
TIP48  
TIP50

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
www.centalsemi.com

R2 (21-September 2003)



145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
www.centrasemi.com